

74LVC1G07

Buffer with open-drain output

Rev. 08 — 17 July 2007

Product data sheet

1. General description

The 74LVC1G07 provides the non-inverting buffer.

The output of this device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment.

Schmitt-trigger action at all inputs makes the circuit tolerant for slower input rise and fall time.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- -24 mA output drive ($V_{CC} = 3.0$ V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC1G07GW	−40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74LVC1G07GV	−40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753
74LVC1G07GM	−40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74LVC1G07GF	−40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891

4. Marking

Table 2. Marking

Type number	Marking code
74LVC1G07GW	VS
74LVC1G07GV	V07
74LVC1G07GM	VS
74LVC1G07GF	VS

5. Functional diagram

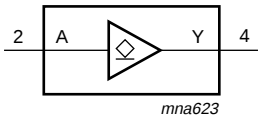


Fig 1. Logic symbol



Fig 2. IEC logic symbol

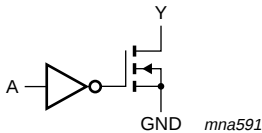


Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

74LVC1G07

Pin 1: n.c., Pin 2: A, Pin 3: GND, Pin 4: Y, Pin 5: V_{CC}

001aab622

Fig 4. Pin configuration SOT353-1 and SOT753

74LVC1G07

Pin 1: n.c., Pin 2: A, Pin 3: GND, Pin 4: Y, Pin 5: n.c., Pin 6: V_{CC}

001aab623

Transparent top view

Fig 5. Pin configuration SOT886

74LVC1G07

Pin 1: n.c., Pin 2: A, Pin 3: GND, Pin 4: Y, Pin 5: n.c., Pin 6: V_{CC}

001aag422

Transparent top view

Fig 6. Pin configuration SOT891

6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT353-1/SOT753	SOT886/SOT891	
n.c.	1	1	not connected
A	2	2	data input
GND	3	3	ground (0 V)
Y	4	4	data output
n.c.	-	5	not connected
V _{CC}	5	6	supply voltage

7. Functional description

Table 4. Function table^[1]

Input A	Output Y
L	L
H	Z

[1] H = HIGH voltage level;
L = LOW voltage level;
Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
I_{IK}	input clamping current	$V_I < 0$ V	-50	-	mA
V_I	input voltage		[1] -0.5	+6.5	V
I_{OK}	output clamping current	$V_O < 0$ V	-50	-	mA
V_O	output voltage	Active mode	[1] -0.5	+6.5	V
		Power-down mode	[1][2] -0.5	+6.5	V
I_O	output current	$V_O = 0$ V to 6.5 V	-	50	mA
I_{CC}	supply current		-	100	mA
I_{GND}	ground current		-100	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[3] -	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When $V_{CC} = 0$ V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
For XSON6 packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage	Active mode	0	-	5.5	V
		Power-down mode; $V_{CC} = 0$ V	0	-	5.5	V
T_{amb}	ambient temperature		-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.65$ V to 2.7 V	-	-	20	ns/V
		$V_{CC} = 2.7$ V to 5.5 V	-	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65V _{CC}	-	-	0.65V _{CC}	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
		V _{CC} = 4.5 V to 5.5 V	0.7V _{CC}	-	-	0.7V _{CC}	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	0.35V _{CC}	-	0.35V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	0.3V _{CC}	-	0.3V _{CC}	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = 100 µA; V _{CC} = 1.65 V to 5.5 V	-	-	0.10	-	0.10	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	-	0.70	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.30	-	0.45	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.40	-	0.60	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.55	-	0.80	V
		I _O = 32 mA; V _{CC} = 4.5 V	-	-	0.55	-	0.80	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	^[2]	±0.1	±5	-	±100	µA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 5.5 V	-	±0.1	±10	-	±100	µA
I _{OFF}	power-off leakage current	V _I or V _O = 5.5 V; V _{CC} = 0 V	-	±0.1	±10	-	±200	µA
I _{CC}	supply current	V _I = 5.5 V or GND; I _O = 0 A; V _{CC} = 1.65 V to 5.5 V	-	0.1	10	-	200	µA
ΔI _{CC}	additional supply current	per pin; V _I = V _{CC} – 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	^[2]	5	500	-	5000	µA
C _I	input capacitance	V _{CC} = 3.3 V; V _I = GND to V _{CC}	-	5.0	-	-	-	pF

[1] All typical values are measured at T_{amb} = 25 °C.

[2] These typical values are measured at V_{CC} = 3.3 V.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for load circuit see [Figure 8](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t_{pd}	propagation delay	A to Y; see Figure 7 ^[2]						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1.0	2.6	6.7	1.0	8.4	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0.5	1.7	5.5	0.5	7.0	ns
		$V_{CC} = 2.7 \text{ V}$	0.5	2.3	4.7	0.5	6.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.5	2.2	4.2	0.5	5.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.5	1.6	3.5	0.5	4.5	ns
C_{PD}	power dissipation capacitance	$V_I = \text{GND to } V_{CC}; V_{CC} = 3.3 \text{ V}$ ^[3]	-	7.0	-	-	-	pF

[1] Typical values are measured at $T_{amb} = 25 \text{ °C}$ and $V_{CC} = 1.8 \text{ V}, 2.5 \text{ V}, 2.7 \text{ V}, 3.3 \text{ V}$ and 5.0 V respectively.

[2] t_{pd} is the same as t_{PLZ} and t_{PZL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

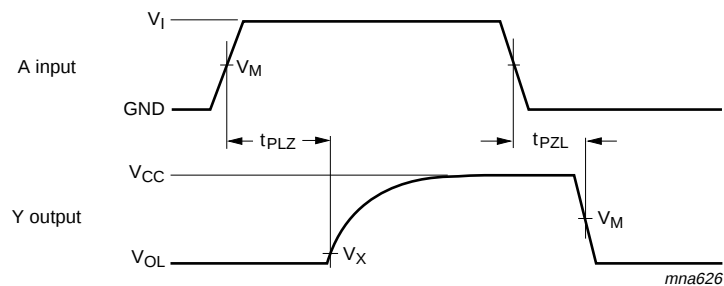
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



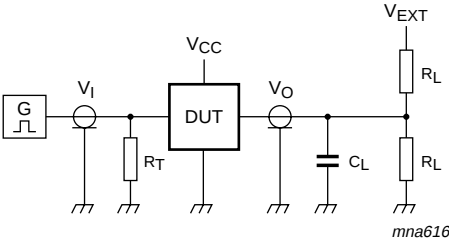
Measurement points are given in [Table 9](#).

V_{OL} is the typical output voltage level that occurs with the output load.

Fig 7. The input (A) to output (Y) propagation delays

Table 9. Measurement points

Supply voltage	Input	Output	
V _{CC}	V _M	V _M	V _X
1.65 V to 1.95 V	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.15 V
2.3 V to 2.7 V	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.15 V
2.7 V	1.5 V	1.5 V	V _{OL} + 0.3 V
3.0 V to 3.6 V	1.5 V	1.5 V	V _{OL} + 0.3 V
4.5 V to 5.5 V	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.3 V



Test data is given in [Table 10](#).
Definitions for test circuit:
RL = Load resistance.
CL = Load capacitance including jig and probe capacitance.
RT = Termination resistance should be equal to the output impedance Z₀ of the pulse generator.
V_{EXT} = External voltage for measuring switching times.

Fig 8. Load circuit for switching times

Table 10. Test data

Supply voltage	Input		Load		V _{EXT}
V _{CC}	V _I	t _r , t _f	C _L	R _L	t _{pZL} , t _{pLZ}
1.65 V to 1.95 V	V _{CC}	≤ 2.0 ns	30 pF	1 kΩ	2V _{CC}
2.3 V to 2.7 V	V _{CC}	≤ 2.0 ns	30 pF	500 Ω	2V _{CC}
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	6 V
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	6 V
4.5 V to 5.5 V	V _{CC}	≤ 2.5 ns	50 pF	500 Ω	2V _{CC}

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mmSOT353-1

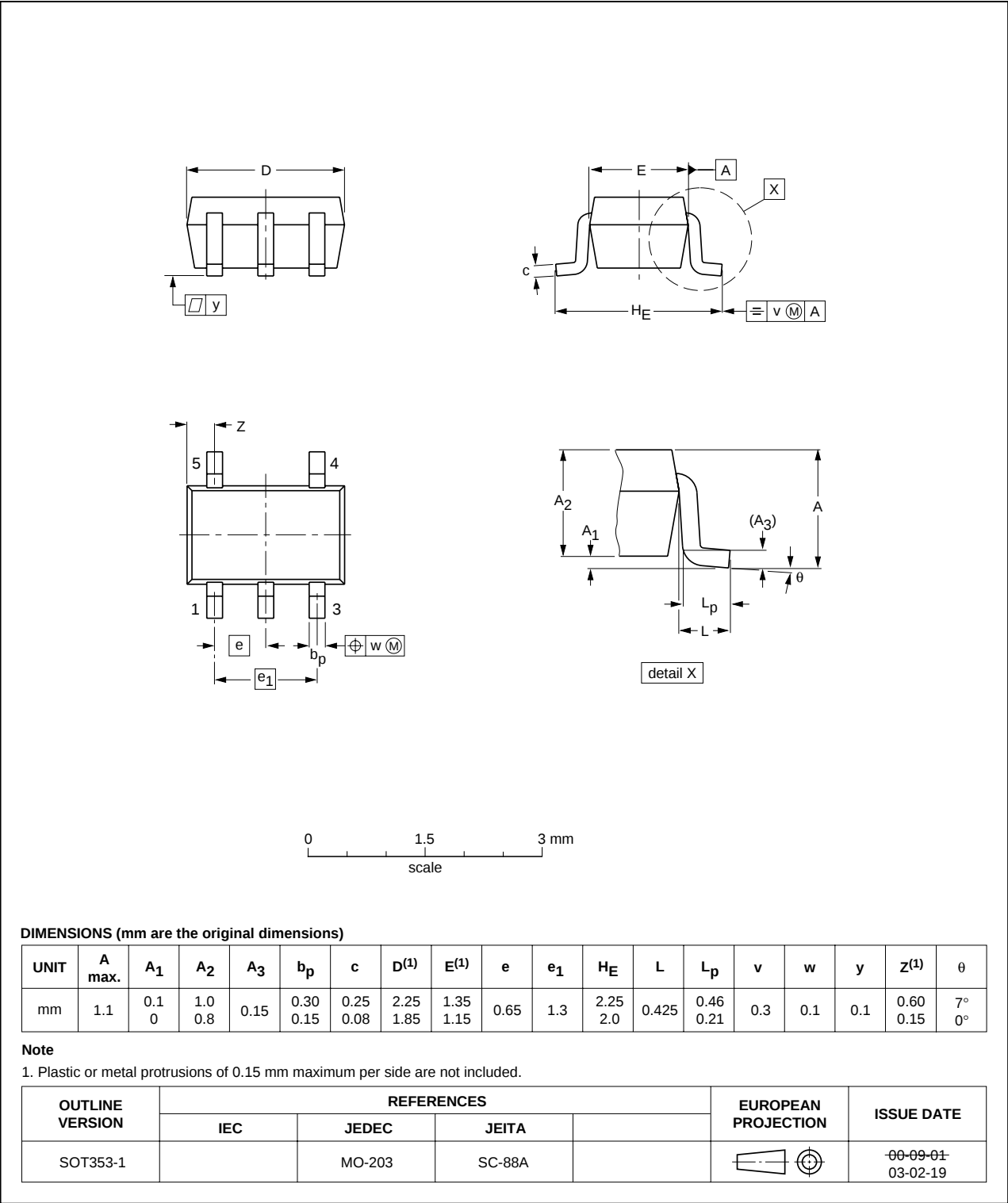


Fig 9. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753



Fig 10. Package outline SOT753 (SC-74A)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

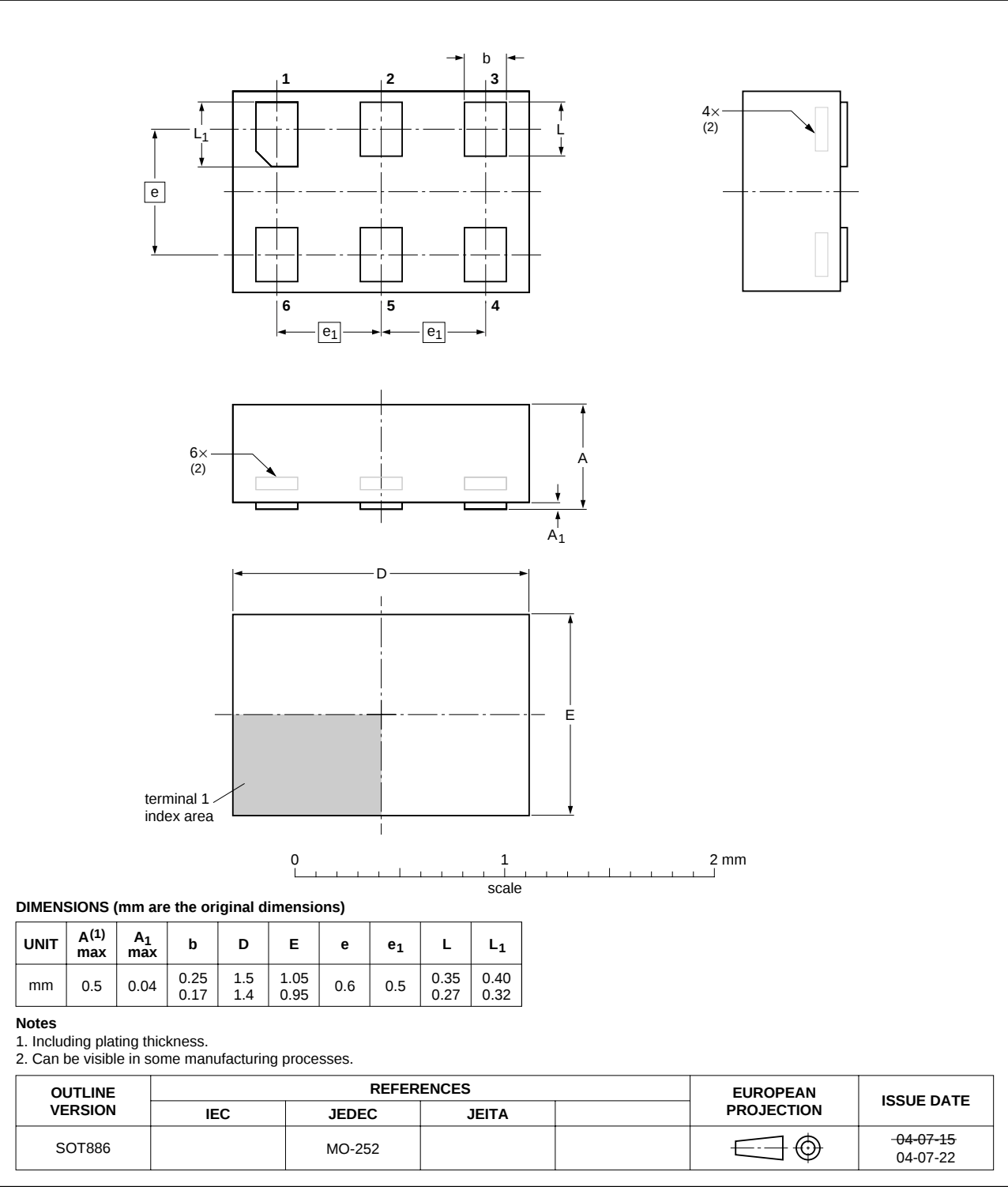


Fig 11. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

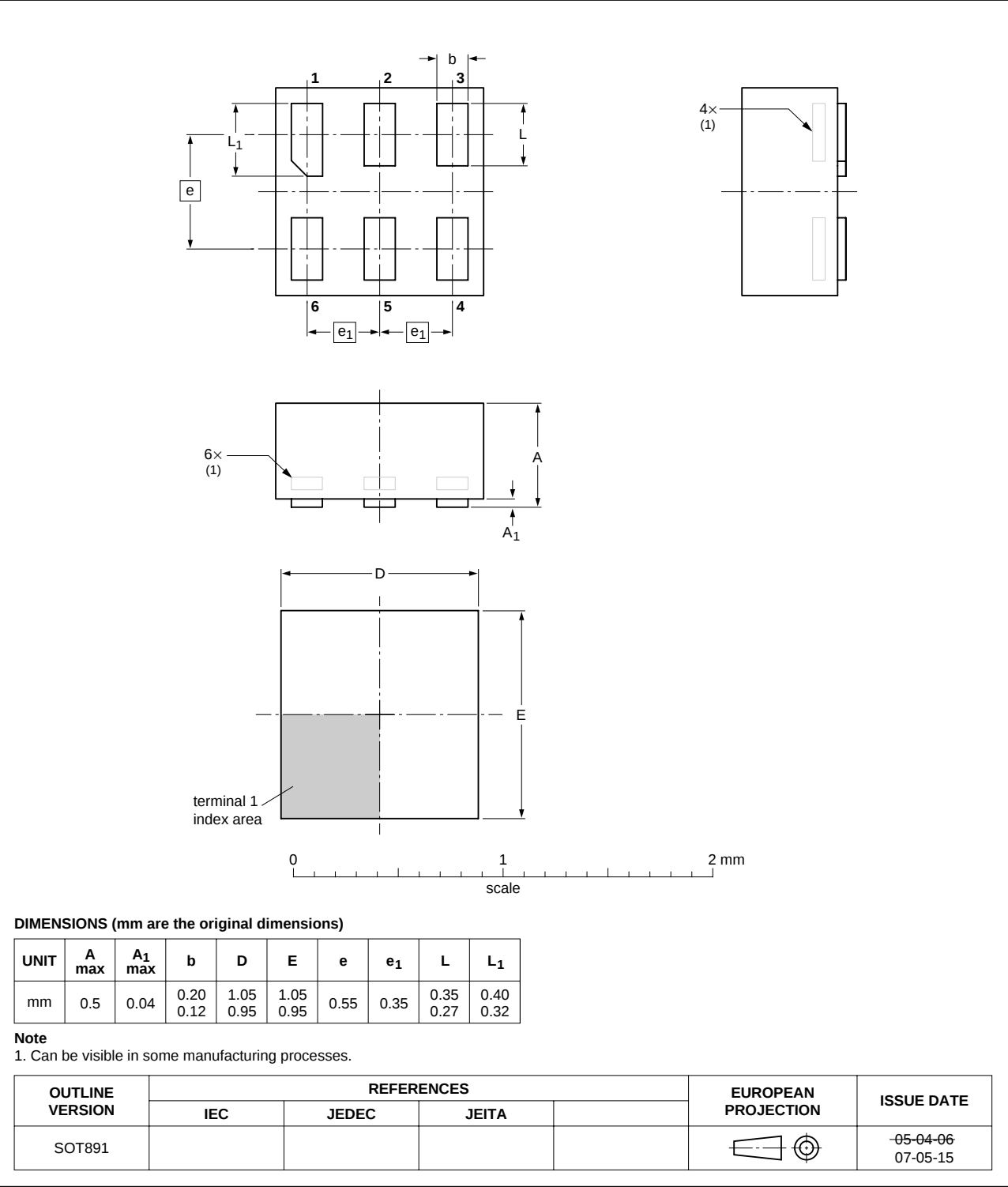


Fig 12. Package outline SOT891 (XSON6)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G07_8	20070717	Product data sheet	-	74LVC1G07_7
Modifications:	• New package outline drawing for XSON6/SOT891.			
74LVC1G07_7	20070515	Product data sheet	-	74LVC1G07_6
74LVC1G07_6	20040907	Product data sheet	-	74LVC1G07_5
74LVC1G07_5	20030307	Product data sheet	-	74LVC1G07_4
74LVC1G07_4	20021002	Product data sheet	-	74LVC1G07_3
74LVC1G07_3	20020528	Product data sheet	-	74LVC1G07_2
74LVC1G07_2	20010406	Product data sheet	-	74LVC1G07_1
74LVC1G07_1	20001122	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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